TSTE85 FORMULAS

Circuits

Transition activity $\alpha = \alpha_{01} + \alpha_{10} = 2\alpha_{01} = 2\alpha_{10}$

Switch activity $a = \sum_i \alpha_{01,i} C_i \Big/ \sum_i C_i$

Switched capacitance $C_{sw} = a \sum_i C_i$

Dynamic power consumption $P_d = f_{clk} C_{sw} V_{pp} V_{DD}$

Short-circuit power consumption $P_{sc} = a f_{clk} t_{sc} I_{peak} V_{DD}$

Propagation time $t_p \propto V_{DD} \Big/ \left(V_{DD} - V_T\right)^r$, $1 \le r \le 2$

MOSFETs

Threshold voltage $V_T = V_{T0} + \gamma\left(\sqrt{\left|V_{SB} - 2\Phi_F\right|} - \sqrt{\left|2\Phi_F\right|}\right)$

Weak inversion ($V_{GT} < 0$) $I_D = I_{D0}\left(W/L\right) e^{-\left|V_{GT}\right| / \left(n_s V_\Theta\right)} \left(1 + \lambda V_{DS}\right)$

where

$V_\Theta \approx 26$ mV @ $T = 300$ K

n_s can be calculated from $S = n_s V_\Theta \ln(10)$

Strong inversion ($V_{GT} \ge 0$) $I_D = k'\left(W/L\right) V_{min} \left(\left|V_{GT}\right| - V_{min}/2\right)\left(1 + \lambda V_{DS}\right)$

where

$V_{min} = \min(|V_{GT}|, |V_{DS}|, |V_{DSAT}|)$ (corresponding to *saturation*, *resistive*, and *velocity saturation* modes)

Gate-oxide leakage $I_G = k_1 W \left(V_{ox}/t_{ox}\right)^2 e^{-k_2 t_{ox}/V_{ox}}$

Logic

Shannon's expansion theorem $\overline{f\left(x, y, z, \ldots, +, \cdot\right)} = f\left(\bar{x}, \bar{y}, \bar{z}, \ldots, \cdot, +\right)$

Cofactors $f_{\bar{x}} = f\left(x, y, z, \ldots\right)\Big|_{x=0}$, $f_x = f\left(x, y, z, \ldots\right)\Big|_{x=1}$

Expansion in sum and product $f\left(x, y, z, \ldots\right) = \bar{x} \cdot f_{\bar{x}} + x \cdot f_x = \left(x + f_{\bar{x}}\right)\left(\bar{x} + f_x\right)$

Observability Don't Care set $\mathrm{ODC}_x = f_{\bar{x}} f_x + \overline{f_{\bar{x}}}\,\overline{f_x}$